

L Number	Hits	Search Text	DB	Time stamp
1	1609482	memory or storage	USPAT; US-PPGPUB; EPO; JPO	2003/04/05 13:17
2	87775	(memory or storage) and (nonvolatile or non-volatile or floating adj gate)	USPAT; US-PPGPUB; EPO; JPO	2003/04/05 13:18
3	23	((memory or storage) and (nonvolatile or non-volatile or floating adj gate)) and (voltage or potential or level) with cell with (current or voltage or time or frequency) with (sinusoidal or rectangular or trapezoidal)	USPAT; US-PPGPUB; EPO; JPO	2003/04/05 13:22

L Number	Hits	Search Text	DB	Time stamp
1	1609482	memory or storage	USPAT; US-PGPUB; EPO; JPO	2003/04/04 10:27
2	1627	(memory or storage) and set with sens\$5 with read\$5 with memory	USPAT; US-PGPUB; EPO; JPO	2003/04/04 10:29
3	1265	((memory or storage) and set with sens\$5 with read\$5 with memory) and (parameter or current or voltage or time or frequency) with read\$5	USPAT; US-PGPUB; EPO; JPO	2003/04/04 10:30
4	319	((((memory or storage) and set with sens\$5 with read\$5 with memory) and (parameter or current or voltage or time or frequency) with read\$5) and floating adj gate	USPAT; US-PGPUB; EPO; JPO	2003/04/04 10:33
5	74	((((memory or storage) and set with sens\$5 with read\$5 with memory) and (parameter or current or voltage or time or frequency) with read\$5) and floating adj gate) and noise	USPAT; US-PGPUB; EPO; JPO	2003/04/04 10:42
6	17	((((((memory or storage) and set with sens\$5 with read\$5 with memory) and (parameter or current or voltage or time or frequency) with read\$5) and floating adj gate) and noise) and read\$5 with noise with (reduc\$3 or decreas\$3)	USPAT; US-PGPUB; EPO; JPO	2003/04/04 10:43

L Number	Hits	Search Text	DB	Time stamp
1	1609482	memory or storage	USPAT; US-PGPUB; EPO; JPO	2003/04/04 10:54
2	87775	(memory or storage) and (nonvolatile or non-volatile or floating adj gate)	USPAT; US-PGPUB; EPO; JPO	2003/04/04 10:56
3	0	((memory or storage) and (nonvolatile or non-volatile or floating adj gate)) and appl\$5 with set with voltage with episodic adj stimulus	USPAT; US-PGPUB; EPO; JPO	2003/04/04 11:30
4	14979	((memory or storage) and (nonvolatile or non-volatile or floating adj gate)) and (voltage or potential or level) with cell	USPAT; US-PGPUB; EPO; JPO	2003/04/04 11:32
5	49	((memory or storage) and (nonvolatile or non-volatile or floating adj gate)) and (voltage or potential or level) with cell) and measur\$5 with (parameter or current or voltage or time or frequency) with noise	USPAT; US-PGPUB; EPO; JPO	2003/04/04 11:34
6	5	((((memory or storage) and (nonvolatile or non-volatile or floating adj gate)) and (voltage or potential or level) with cell) and measur\$5 with (parameter or current or voltage or time or frequency) with noise) and (voltage or potential or level) with (parameter or current or voltage or time or frequency) with noise with (reduc\$5 or decreas\$5)	USPAT; US-PGPUB; EPO; JPO	2003/04/04 11:40
7	926	((memory or storage) and (nonvolatile or non-volatile or floating adj gate)) and apply\$5 with set with voltages	USPAT; US-PGPUB; EPO; JPO	2003/04/04 11:41
8	2515	((memory or storage) and (nonvolatile or non-volatile or floating adj gate)) and apply\$5 with set with voltages) aand determin\$5 with conduction with set with voltages	USPAT; US-PGPUB; EPO; JPO	2003/04/04 11:42
9	1	((memory or storage) and (nonvolatile or non-volatile or floating adj gate)) and apply\$5 with set with voltages) and determin\$5 with conduction with set with voltages	USPAT; US-PGPUB; EPO; JPO	2003/04/04 11:45
10	380	((memory or storage) and (nonvolatile or non-volatile or floating adj gate)) and (voltage or potential or level) with memory with interval	USPAT; US-PGPUB; EPO; JPO	2003/04/04 12:51
11	13	((memory or storage) and (nonvolatile or non-volatile or floating adj gate)) and (voltage or potential or level) with memory with interval) and determin\$5 with characteristics with cell	USPAT; US-PGPUB; EPO; JPO	2003/04/04 12:06
13	0	((memory or storage) and (nonvolatile or non-volatile or floating adj gate)) and (voltage or potential or level) with memory with interval) and determin\$5 with current with cell with (vary\$5 or vari\$5) with (voltage or potential or level)	USPAT; US-PGPUB; EPO; JPO	2003/04/04 12:07
12	53	((memory or storage) and (nonvolatile or non-volatile or floating adj gate)) and (voltage or potential or level) with memory with interval) and determin\$5 with current with cell	USPAT; US-PGPUB; EPO; JPO	2003/04/04 12:08
14	24	((memory or storage) and (nonvolatile or non-volatile or floating adj gate)) and (voltage or potential or level) with (vary\$5 or vari\$5) with memory with interval	USPAT; US-PGPUB; EPO; JPO	2003/04/04 12:52